

Silicon PNP Power Transistors

2SA1093

DESCRIPTION

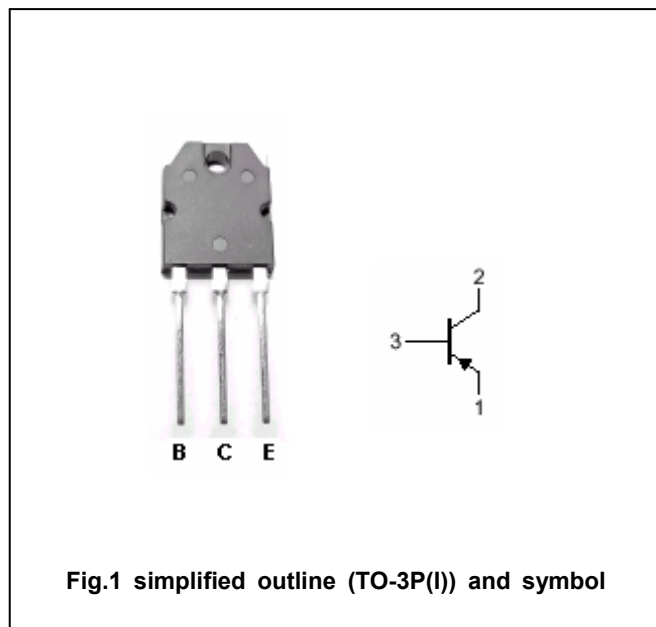
- With TO-3P(I) package
- Complement to type 2SC2563
- High transition frequency

APPLICATIONS

- Audio frequency power amplifier applicatios

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-120	V
V_{CEO}	Collector-emitter voltage	Open base	-120	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-8	A
I_B	Base current		-0.8	A
P_T	Total power dissipation	$T_C=25^\circ\text{C}$	80	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-50mA, I_B=0$	-120			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-4A; I_B=-0.4A$		-1.0	-2.0	V
V_{BE}	Base-emitter voltage	$I_C=-4A; V_{CE}=-5V$		-1.5	-2.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-120V; I_E=0$			-50	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V; I_C=0$			-50	μA
h_{FE-1}	DC current gain	$I_C=-1A; V_{CE}=-5V$	55		240	
h_{FE-2}	DC current gain	$I_C=-4A; V_{CE}=-5V$	30			
f_T	Transition frequency	$I_C=-1A; V_{CE}=-10V$		90		MHz
C_{ob}	Output capacitance	$I_E=0; V_{CB}=-10V; f=1MHz$		150		pF

◆ h_{FE-1} Classifications

R	O	Y
55-110	80-160	120-240

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PACKAGE OUTLINE

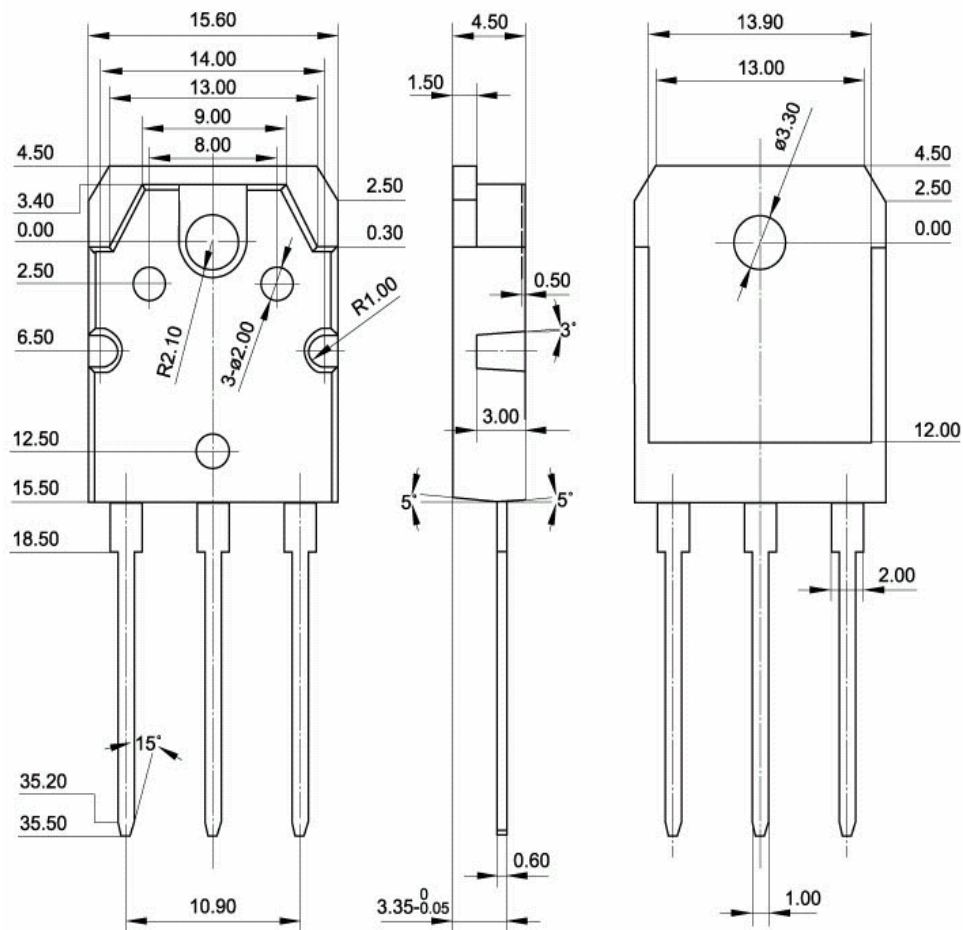


Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)